Publication list Helge Weman (chronological)

Date: June 22, 2014

Internationally refereed journal papers (with interactive links)

1. *Neutral carbon-related complex defects and the annealing of thermal donors in p-type Czochralski silicon*
H. Weman, B. Monemar, and P-O. Holtz,
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2. *Deep-level transient spectroscopy and photoluminescence studies of electron-irradiated Czochralski silicon*
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3. *Thermal donors and carbon-oxygen defects in silicon*
J.L. Lindström, **H. Weman**, and G. Oehrlein,
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4. *Impact ionization of excitons and electron-hole droplets in silicon*
H. Weman, Q.X. Zhao, and B. Monemar,
Phys. Rev. B **36**, 5054-5057 (1987), Rapid Communication.

5. *Impact ionization and electric field quenching of photoluminescence in silicon*
H. Weman, Q.X. Zhao, and B. Monemar,
Solid-St. Electron. **31**, 791-794 (1988).

6. *Luminescence in silicon in electric and magnetic fields*
Q.X. Zhao, **H. Weman**, and B. Monemar,
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7. *Electric field induced quenching of shallow and deep bound excitons in silicon*
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8. *Impact ionization of free excitons and electron-hole droplets in silicon in weak electric and magnetic fields*
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9. *Optical detection of microwave-induced impact ionization of bound excitons in silicon*
H. Weman, M. Godlewski, and B. Monemar,
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10. *Spontaneous oscillations and chaos in Si induced by excitonic impact ionization*
H. Weman, A. Henry, and B. Monemar,
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11. *Electrical and optical properties of gold doped n-type silicon*
H. Weman, A. Henry, T. Begum, B. Monemar, O.O. Awadelkarim, and J.L. Lindström,
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12. *On the core concentration and the formation kinetics of thermal donors in silicon*
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13. *Optically detected magnetic resonance of a thermally induced deep center in electron-irradiated silicon*
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14. *Photoluminescence of defects introduced by deuterium plasmas in silicon*
H. Weman, J.L. Lindström, and G. Oehrlein,
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15. *Reactive-ion- and plasma-etching-induced extended defects in silicon studied with photoluminescence*
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16. *Defect annealing in irradiated boron-doped silicon*
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17. *Strain-induced quantum confinement of carriers due to extended defects in silicon*
H. Weman, B. Monemar, G.S. Oehrlein, and S.J. Jeng,
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18. *Intensity of exciton luminescence in silicon in a weak magnetic field*
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19. *Novel approaches in 2 and 3 dimensional confinement structures: Processing and properties*
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21. *Optical properties of quantum structures fabricated by focused Ga ion beam implantation*
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22. *Impact ionization of excitons and donors in $Al_xGa_{1-x}As$/(n-type GaAs):Si quantum wells*
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36. *Dimensionality effects on strain and quantum-confinement in lattice-mismatched $InAs_xP_{1-x}/InP$ quantum wires*
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H. Weman, (**invited talk**)
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H. Weman, (**invited talk**)
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205. *Importance of initial growth conditions during the growth of III-V nanowires by molecular beam epitaxy*
D.L. Dheeraj, C. Sartel, L. Travers, J.C. Harmand, G. Patriarche, B.-O. Fimland, and **H. Weman**,
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A.F. Moses, D.L. Dheeraj, B.-O. Fimland, **H. Weman**, K.F. Karlsson, and P.O. Holtz,
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208. *Pulsed laser deposition growth of ZnO nanostructures for electron transport in hybrid inorganic/organic solar cells*
C. Weigand, K. Valset, R. Fagerberg, C. Ladam, J.K. Grepstad, **H. Weman**, C.G. Allen, D.J. Baker, T.E. Furtak, and R.T. Collins,
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G.K. Svendsen, **H. Weman**, and J. Skaar,
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210. *Investigation of the structural and optical properties of single GaAs/GaAsSb/GaAs nanowire quantum dots*
A.F. Moses, T.B. Hoang, D.L. Dheeraj, B.-O. Fimland, **H. Weman**, K.F. Karlsson, and P.O. Holtz,
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211. *Modal reflection properties of nanowire waveguides*
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212. *Micro-photoluminescence study of heterostructured GaAs/AlGaAs and GaAs/GaAsSb nanowires grown by molecular beam epitaxy*
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D.L. Dheeraj, G. Patriarche, H.L. Zhou, A.F. Moses, J.C. Harmand, B.-O. Fimland, and **H. Weman**,
15th Int. Conference on Molecular Beam Epitaxy, Vancouver, Canada, Aug. 3-8, 2008.

214. *Radiative emission from a type-II GaAsSb segment in a single GaAs nanowire*
A.F. Moses, D.L. Dheeraj, B.-O. Fimland, **H. Weman**, K.F. Karlsson, and P.O. Holtz,
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215. *Characterization of ZnO thin films grown by pulsed laser deposition for hybrid inorganic/organic solar cells*
C. Weigand, K. Valset, R. Fagerberg, C. Ladam, J.K. Grepstad, **H. Weman**, C.G. Allen, D.J. Baker, T.E. Furtak, and R.T. Collins,
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A.F. Moses, D.L. Dheeraj, B.-O. Fimland, **H. Weman**, K.F. Karlsson, and P.O. Holtz,
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D.L. Dheeraj, G. Patriarche, H. Zhou, A.F. Moses, H.B. Thang, A.T.J. van Helvoort, J.C. Harmand, B.-O. Fimland, and **H. Weman**,
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C. Weigand, M. Bergren, K. Valset, D. Carey, R. Fagerberg, C. Ladam, J.K. Grepstad, **H. Weman**, T.E. Furtak, and R.T. Collins,
1st Int. Nanosymposium@NTNU, Trondheim, Norway, Sept. 11-12, 2008.

219. *Growth, structural and optical characterizations of GaAs/AlGaAs core-shell nanowires*
H. Zhou, D.L. Dheeraj, T.B. Hoang, A.F. Moses, B.-O. Fimland, **H. Weman**, A.T.J. van Helvoort, L. Liu and J.C. Harmand, 3rd Int. Workshop on Nanowire Growth Mechanisms, Duisburg, Germany, Sept. 15-16, 2008.

220. *A novel effect of Sb on the crystalline structure of GaAs nanowires grown by MBE*
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221. *Optical properties of single wurtzite GaAs nanowires and GaAs nanowires with GaAsSb inserts*
T.B. Hoang, H. Zhou, A.F. Moses, D.L. Dheeraj, A.T.J. van Helvoort, B.-O. Fimland, and **H. Weman**, Materials Res. Soc. 2008 Fall Meeting, Symposium LL: Nanowires - Synthesis, Properties, Assembly, and Applications, Boston, USA, Dec. 1-5, 2008. Proceedings **Vol. 1144**, p. LL02-02, (2009). DOI: 10.1557/PROC-1144-LL02-02.

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D.J. Baker, C.G. Allen, J.M. Albin, H.E. Oertli, M.R. Bergren, T.D. Berman, T.E. Furtak, R.T. Collins, D.C. Olson, M.S. White, D.S. Ginley, C. Ladam, C. Weigand, K. Valset, J. Grepstad, and **H. Weman**,
Materials Res. Soc. 2008 Fall Meeting, Symposium H: Physics and Technology of Organic Semiconductor Devices, Boston, USA, Dec. 1-5, 2008.

223. *Structural and optical characterization of single hetero-structured III-V nanowires grown by MBE*
H. Weman, (**invited talk**)
1st Int. Conf. on Transport and Optical Properties of Nanomaterials, Allahabad, India, Jan.5-8, 2009.

224. *Heterostructured wurtzite/zinc-blende GaAs/GaAsSb nanowires: New possibilities for band-structure engineering in nanowire based photonic devices*
H. Weman, (**invited talk**)
2009 RCIQE International Seminar on "Advanced Semiconductor Materials and Devices", Sapporo, Japan, March 2-3, 2009

225. *Pulsed laser deposition of ZnO nanostructures for hybrid inorganic/organic solar cells*
D. Skåre, C. Weigand, A.-S. Vardøy, C. Ladam, Ø. Dahl, M. Bergren, R. Fagerberg, **H. Weman**, T. Furtak, and R. Collins, Norwegian Photovoltaic workshop, Oppdal, Norway, March 19-21, 2009.

226. *Cool, Small and Bright: cryogenic micro-photoluminescence for photovoltaic materials*
A. Røyset, R. Fagerberg, and **H. Weman**,
Norwegian Photovoltaic workshop, Oppdal, Norway, March 19-21, 2009

227. *Characterization of ZnO thin films and nanostructures grown by pulsed laser deposition*
C. Weigand, M. Bergren, A.-S. Vardøy, K. Valset, D. Carey, C. Ladam P.E. Vullum, J. Walmsley, R. Fagerberg, T. Furtak, and R. Collins, J. Grepstad, **H. Weman**, Materials Res. Soc. 2009 Spring Meeting, Symposium V: Functional Metal-Oxide Nanostructures, San Francisco, USA, April 14-17, 2009. Proceedings Vol. **1174**, p. V07-09 (2009).

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A.F. Moses, T.B. Hoang, H. Zhou, D.L. Dheeraj, B.O. Fimland, and **H. Weman**,
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230. *Modeling of electronic and optical properties of semiconductor nanowires*
G.K. Svendsen, M.-A. Dupertuis, **H. Weman**, and J. Skaar,
NANOMAT Conference, Lillehammer, Norway, June 15-17, 2009.

231. *Structural characterization of semiconductor nanowire heterostructures using conventional transmission electron microscopy techniques*
A.T. J. van Helvoort, D.L. Dheeraj, S. Grønsberg, G. Patriarche, H. Zhou, T.B. Hoang, A.F. Moses, B.-O. Fimland, and **H. Weman**,
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232. *Wurtzite GaAs and zinc blende GaAsSb nanowires: New possibilities for heterostructure engineering*
T.B. Hoang, A.F. Moses, H. Zhou, D.L. Dheeraj, A.T J. van Helvoort , B.-O. Fimland, and **H. Weman**,
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233. *Nanostructured ZnO layers grown by pulsed laser deposition for hybrid inorganic/organic solar cells*
C. Ladam, C. Weigand, D. Skåre, A.-S. Vardøy, Ø. Dahl, M. Bergren, R. Fagerberg, **H. Weman**, T. Furtak, and R. Collins, NANOMAT Conference, Lillehammer, Norway, June 15-17, 2009.

234. *Diffusion-limited growth of GaAs nanowires by molecular beam epitaxy*
D.L. Dheeraj, E. Rogstad, M. Scheffler, H.L. Zhou, A.T.J. van Helvoort, B.O. Fimland, **H. Weman**, G. Patriarche, and J.C. Harmand,
Nanofils et Nanotubes Semiconducteurs, Autrans, France, June 30-July 3, 2009.

235. *Self-organized wurtzite AlGaAs core-shell nanowires with GaAs inserts grown by molecular beam epitaxy*
H.L. Zhou, T.B. Hoang, D.L. Dheeraj, A.F. Moses, A.T.J. van Helvoort, B.O. Fimland, **H. Weman**, G. Patriarche, and J.C. Harmand,
GDR Semiconductor Nanowires and Nanotubes, Autrans, France, June 30-July 3, 2009.

236. *Modeling of optical and electronic properties of semiconductor nanowires*
G.K. Svendsen, M.-A. Dupertuis, **H. Weman**, and J. Skaar,
Northern Optics, Vilnius, Lithuania, Aug. 26-28, 2009.

237. *Dark field transmission electron microscopy techniques for structural characterization of semiconductor nanowire heterostructures*
A.T.J. van Helvoort, D.L. Dheeraj, H.L. Zhou, S. Grønsberg, G. Patriarche, B.-O. Fimland, and **H. Weman**
EMAG 2009 Microscopy at the nanoscale and beyond, Sheffield, UK, Sept. 8-11, 2009.
Journal of Physics, Conference Series, **241**, 012084 (2010)

238. *Photonic nanowires for solar cell applications*
T.B. Hoang, A.F. Moses, H.L. Zhou, D.L. Dheeraj, A.T.J. van Helvoort, B-O. Fimland, and **H. Weman**, 4th KIFEE Symp. on Environment, Energy, Materials and Education, Trondheim, Norway, Sept. 6-9, 2009.

239. *Optimization of heterointerfaces in axial heterostructured nanowires grown by molecular beam epitaxy*
D.L. Dheeraj, A.T J. van Helvoort, A.F. Moses, H. Zhou, T.B. Hoang, B.-O. Fimland, **H. Weman**, and G. Patriarche, 4th Int. Workshop on Nanowire Growth Mechanisms, Paris, France, Oct. 26-27, 2009.

240. *Polarized micro-photoluminescence imaging of single GaAs/AlGaAs core-shell nanowires with GaAsSb inserts*
T.B. Hoang, A.F. Moses, H. Zhou, D.L. Dheeraj, A.T J. van Helvoort , B.-O. Fimland, and **H. Weman**,
Materials Res. Soc. 2009 Fall Meeting, Symposium O: Excitons and Plasmon Resonances in Nanostructures II, Boston, MA, USA, Nov. 29 - Dec. 4, 2009.

241. *Effect of growth-interruption on structural and optical properties of GaAs/GaAsSb axial heterostructured nanowires*
D.L. Dheeraj, A.T J. van Helvoort, A.F. Moses, H. Zhou, T.B. Hoang, B.-O. Fimland, and **H. Weman**,
Materials Res. Soc. 2009 Fall Meeting, Symposium M: Multifunction at the Nanoscale through Nanowires, Boston, MA, USA, Nov. 29 - Dec. 4, 2009.

242. *Growth and structural characterization of axial heterostructured GaAs/GaSb nanowires grown by molecular beam epitaxy*
D.L. Dheeraj, G. Patriarche, A.T.J. Van Helvoort, H.L. Zhou, B.O. Fimland, and **H. Weman,**
3rd International conf. on One-dimensional Nanomaterials, Atlanta, GA, Dec. 7-9, 2009.

243. *Crystal phase dependent photoluminescence polarization in single semiconductor nanowires*
T.B. Hoang, A.F. Moses, H.L. Zhou, D.L. Dheeraj, A.T.J. van Helvoort, B.-O. Fimland, and **H. Weman**
3rd International conf. on One-dimensional Nanomaterials, Atlanta, GA, Dec. 7-9, 2009.

244. *Heterostructured III-V nanowires with mixed crystal phases: New possibilities for band structure engineering*
H. Weman, Post dead line talk,
3rd International conf. on One-dimensional Nanomaterials, Atlanta, GA, Dec. 7-9, 2009.

245. *Growth of heterostructured III-V nanowires by molecular beam epitaxy for photonic applications*
D.L. Dheeraj, H.L. Zhou, A.F. Moses, T.B. Hoang, A.T.J. Van Helvoort, B.O. Fimland, and **H. Weman**
(**invited talk**)
SPIE Photonics West, Quantum Sensing and Nanophotonic Devices, San Francisco, CA, Jan. 24-28, 2010.
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246. *Structural and optical probing of single III-V nanowires with different crystal phases*
H. Weman, (**invited talk**)
NorPRINS workshop, Oslo, Norway, March 4-5, 2010.

247. *Tuning of the crystal phase in III-V nanowires grown by Au-assisted molecular beam epitaxy*
D.L. Dheeraj, A.T.J. van Helvoort, A.F. Moses, T.B. Hoang, B.O. Fimland, **H. Weman**,
Materials Res. Soc. 2010 Spring Meeting, Symposium P: Semiconductor Nanowires: Growth, Physics, Devices, and Applications, San Francisco, CA, USA, April 5-9, 2010.

248. *Surface modification of Zinc Oxide anodes in organic solar cells*
T. E. Furtak, D. J. Baker, C. C. Weigand, J. M. Adamson, C. G. Allen, A. E. Yocom, L. S. Patterson, **H. Weman**, C. Ladam, D. C. Olson, D. S. Ginley and R. T. Collins,
Materials Res. Soc. 2010 Spring Meeting, Symposium HH: Organic Photovoltaic Science and Technology, San Francisco, CA, USA, April 5-9, 2010.

249. *Modelling of reflection properties of nanowire lasers*
G.K. Svendsen, **H. Weman**, and J. Skaar,
Norwegian Electro-Optics meeting, Ålesund, Norway, April 7-9, 2010.

250. *Photoluminescence characterization of ZnO nanorods*
C. Ladam, and **H. Weman**, M. Vetaas Thomassen, C. Weigand, and A. Røyset,
Norwegian Electro-Optics meeting, Ålesund, Norway, April 7-9, 2010.

251. *Micro-photoluminescence spectroscopy and imaging of single axial and radial heterostructured III-V nanowires*
A.F. Moses, L. Ahtapodov, T.B. Hoang, D.L. Dheeraj, A.T.J. van Helvoort, B.O. Fimland and **H. Weman**,
Norwegian Electro-Optics meeting, Ålesund, Norway, April 7-9, 2010.

252. *ZnO nanorod hybrid organic/inorganic solar cells and the effect of surface modifications*
C. Weigand, D.J. Baker, J.M. Adamson, C.G. Allen, M.R. Bergren, K.X. Steirer, D.C. Olson, C. Ladam, D.S. Ginley, R.T. Collins, and T.E. Furtak, and **H. Weman**,
Renewable Energy Research Conference, Trondheim, Norway, June 7-10, 2010.

253. *Photocurrent spectroscopy of single wurtzite GaAs nanowires*
D.C. Kim, L. Ahtapodov, A.B. Boe, J.W. Choi, H. Ji, G.T. Kim, A.F. Moses, D.L. Dheeraj, B.O. Fimland, and **H. Weman**, 30th Int. Conf. on the Physics of Semiconductors, Seoul, South Korea, July 25-30, 2010.
Proc. AIP Conference Proceedings Volume 1399, 429 (2011).

254. *Photoluminescence polarization anisotropy in a single heterostructured III-V nanowire with mixed crystal phases*
A.F. Moses, L. Ahtapodov, T.B. Hoang, D.L. Dheeraj, A.T.J. van Helvoort, B.O. Fimland and **H. Weman**,
30th Int. Conf. on the Physics of Semiconductors, Seoul, South Korea, July 25-30, 2010.

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255. *Controlling crystal phases in GaAs nanowires grown by Au-assisted molecular beam epitaxy*
D.L. Dheeraj, A.M. Munshi, A.T.J. van Helvoort, B.O. Fimland, and **H. Weman**,
16th Int. Conference on Molecular Beam Epitaxy, Berlin, Germany, Aug. 22-27, 2010.

256. *Control of wurtzite and zinc blende crystal phases in single GaAs nanowires grown by Au-assisted MBE*
D.L. Dheeraj, A.M. Munshi, A.T J. van Helvoort, B.-O. Fimland, **H. Weman**,
5th Int. Workshop on Nanowire Growth Mechanisms, Rome, Italy, Nov. 4-5, 2010.

257. *ZnO nanosheets grown by pulsed laser deposition*
C. Weigand, J. Grepstad, **H. Weman**, C. Ladam, P.-E. Vullum, Ø. Dahl, R. Fagerberg, R.T. Collins, and T.E. Furtak, 5th Int. Workshop on Nanowire Growth Mechanisms, Rome, Italy, Nov. 4-5, 2010.

258. *Hetetrostructured III-V nanowires grown by Au-assisted molecular beam epitaxy*
H. Weman, (**invited talk**),
Heraeus workshop on "III-V Nanowires", Bad Honnef, Germany, Feb. 21-23, 2011.

259. *Photocurrent spectroscopy of single wurtzite GaAs nanowires*
D.C. Kim, L. Ahtapodov, A.B. Boe, J.W. Choi, H. Ji, G.T. Kim, A.F. Moses, D.L. Dheeraj, B.O. Fimland, and **H. Weman**, Heraeus workshop on "III-V Nanowires", Bad Honnef, Germany, Feb. 21-23, 2011.

260. *Correlated micro-photoluminescence and electron microscopy studies of individual heterostructured semiconductor nanowires*
J. Todorovic, A.F. Moses, T. Karlberg, D.L. Dheeraj, P. Olk, B.O. Fimland, **H. Weman** and A.T.J. van Helvoort, 17th Int. Conf. on Microscopy of Semiconducting Materials, Cambridge, UK, April 4-7, 2011. Journal of Physics, Conference Series 326, 012043 (2011).

261. *Consecutive photoluminescence and transmission electron microscopy studies of single GaAs/AlGaAs core-shell nanowires with a GaAsSb insert*
A.F. Moses, J. Todorovic, T. Karlberg, A.T.J. van Helvoort, D.L. Dheeraj, P. Olk, B.O. Fimland, and **H. Weman,** Materials Res. Soc. 2011 Spring Meeting, Symposium EE: Semiconductor Nanowires- From Fundamentals to Applications", San Francisco, CA, USA, April 26-29, 2011.

262. *Insights into growth mechanisms of self-catalyzed GaAs nanowires grown by molecular beam epitaxy*
A.M. Munshi, D.L. Dheeraj, J. Todorovic, A.T.J. van Helvoort, B.O. Fimland and **H. Weman**,
Materials Res. Soc. 2011 Spring Meeting, Symposium EE: Semiconductor Nanowires- From Fundamentals to Applications", San Francisco, CA, USA, April 26-29, 2011.

263. *Semiconductor nanowire based solar cells-A Nordic top-level research initiative*
H. Weman, 24th Nordic semiconductor meeting, Fuglsøcenter, Denmark, June 19-22, 2011.

264. *III-V nanowires for high-efficiency solar cells*
H. Weman, (invited talk)
Norway-China Workshop on "Nanotechnology for renewable energy materials", Trondheim, Norway, Aug. 31-Sept. 1, 2011.

265. *Heterostrucured III-V nanowires grown by Au- and self-assisted molecular beam epitaxy*
H. Weman, (invited talk),
PDI Topical Workshop on MBE-grown arsenide nanowires, Berlin, Germany, Sept. 8-9, 2011.

266. *Growth of ZnO nanostructures on c- and a-plane sapphire by Au-assisted pulsed laser deposition*
C. Weigand, D. Skåre, J. Tveit, C. Ladam, R. Holmestad, J. Grepstad, **H. Weman**,
GDR Semiconductor Nanowires and Nanotubes, Porquerolles, France, Oct. 17-21, 2011.

267. *Optical properties of Wurtzite GaAs nanowires*
L. Ahtapodov, P. Olk, J. Todorovic, M. Eriksson, D.L. Dheeraj, A.T.J van Helvoort, P. Bergman, B.O. Fimland, and **H. Weman,**
GDR Semiconductor Nanowires and Nanotubes, Porquerolles, France, Oct. 17-21, 2011.

268. *Periodic arrays of self-catalyzed heterostructured GaAs nanowires on Si substrates grown by molecular beam epitaxy*
A.M. Munshi, D.L. Dheeraj, D.C. Kim, A.T.J. van Helvoort, B.O. Fimland, and **H. Weman,**
GDR Semiconductor Nanowires and Nanotubes, Porquerolles, France, Oct. 17-21, 2011.

269. *Contacting of single nanowires by confocal photodeposition of metal*
P. Olk, T. Härtling, D.C. Kim, and **H. Weman**,
GDR Semiconductor Nanowires and Nanotubes, Porquerolles, France, Oct. 17-21, 2011.

270. *All-optical contacting of single nanowires by confocal photodeposition of metal*
P. Olk, T. Härtling, D.C. Kim, and **H. Weman**,
Materials Res. Soc. 2011 Fall Meeting, Symposium BB: Functional Nanowires and Nanotubes, Boston, MA, USA, Nov. 27 - Dec. 2, 2011.

271. *Wurtzite versus zincblende GaAs – A thorough comparison*
L. Ahtapodov, J. Todorovic, P. Olk, D.C. Kim, T. Mjåland, M. Eriksson, D.L. Dheeraj, A.T.J. van Helvoort, P. Bergman, B.O. Fimland, **H. Weman**,
Materials Res. Soc. 2012 Spring Meeting, San Francisco, CA, USA, Apr. 9 - Apr. 13, 2012.

272. *Characterization of the interface between GaAs nanowires and a 111-Si substrate*
V.T. Fauske, A.M. Munshi, D.L. Dheeraj, D.C. Kim, B.O. Fimland, **H. Weman**, and A.T.J. van Helvoort,
Materials Res. Soc. 2012 Spring Meeting, San Francisco, CA, USA, Apr. 9 - Apr. 13, 2012.

273. *Zinc blende and wurtzite GaAs nanowires grown by self-catalyzed molecular beam epitaxy*
A.M. Munshi, D.L. Dheeraj, D.C. Kim, A.T.J. van Helvoort, B.O. Fimland, and **H. Weman**,
Materials Res. Soc. 2012 Spring Meeting, San Francisco, CA, USA, Apr. 9 - Apr. 13, 2012.

274. *Semiconductor nanowire based solar cells -A Nordic top-level research initiative*
D.C. Kim, A.M. Munshi, D.L. Dheeraj, C.G. Lim, V.T. Fauske, A.T.J. van Helvoort, B.O. Fimland, and **H. Weman**, Technoport conference, Trondheim, Norway, Apr. 16 – Apr. 18, 2012.

275. *III-V nanowire solar cells*
H. Weman, (invited talk),
2012 meeting of Norwegian Research Center for Solar Cell Technology, Trondheim, Norway, May 23, 2012.

276. *Correlation of optical and structural properties of single semiconductor heterostructured nanowires*
J. Todorovic, A.F. Moses, L. Ahtapodov, D.L. Dheeraj, B.O. Fimland, **H. Weman**, and A.T.J. van Helvoort, Scandem 2012, Bergen, Norway, June 13 – June 15, 2012.

277. *Combined micro-photoluminescence and electron microscopy investigation of single GaAs nanowires*
L. Ahtapodov, P. Olk, J. Todorovic, D.C. Kim, T. Mjåland, P. Slåttnes, D.L. Dheeraj, A.T.J. van Helvoort, B.O. Fimland, and **H. Weman,**
31st Int. Conf. on the Physics of Semiconductors, Zurich, Switzerland, July 29 – Aug. 3, 2012.

278. *Investigation of wurtzite GaAs nanowires by polarization dependent photocurrent spectroscopy*
D.C. Kim, D.L. Dheeraj, B.O. Fimland, and **H. Weman**,
31st Int. Conf. on the Physics of Semiconductors, Zurich, Switzerland, July 29 – Aug. 3, 2012.

279. *Site-specific, cross-sectional TEM samples of as-grown nanowires by FIB*
V.T. Fauske, A.M. Munshi, D.L. Dheeraj, D.C. Kim, B.O. Fimland, **H. Weman**, and A.T.J. van Helvoort,
15th EMC conference, Manchester, UK, Sept. 16 – Sept. 21, 2012.

280. *Crystal phase tuning in self-catalyzed GaAs nanowires induced by Ga-droplet contact angle*
A.M. Munshi, D.L. Dheeraj, J. Todorovic, A.T.J. van Helvoort, B.O. Fimland, and **H. Weman**,
17th Int. Conference on Molecular Beam Epitaxy, Nara, Japan, Sept. 23 – Sept. 28, 2012.

281. *A generic model and experimental demonstration of epitaxial growth of GaAs nanowires on graphene layers*
A.M. Munshi, D.L. Dheeraj, V.T. Fauske, D.C. Kim, A.T.J. van Helvoort, B.O. Fimland, and **H. Weman**,
17th Int. Conference on Molecular Beam Epitaxy, Nara, Japan, Sept. 23 – Sept. 28, 2012.

282. *Comparison of Be-doped GaAs nanowires grown by Au- and Ga-assisted molecular beam epitaxy*
D.L. Dheeraj, A.M. Munshi, O.M. Christoffersen, D.C. Kim, G. Signorello, H. Riel, A.T.J. van Helvoort, **H. Weman,** and B.O. Fimland,
17th Int. Conference on Molecular Beam Epitaxy, Nara, Japan, Sept. 23 – Sept. 28, 2012.
J. Cryst. Growth **378**, 532 (2013).

283. *Commercialization of nanotechnology*
H. Weman, (invited talk),
2nd Annual Top-level Research Initiative meeting, Helsinki, Finland, Oct. 30, 2012.

284. *III-V nanowires for high-efficiency solar cells*
H. Weman, (invited talk),
Transatlantic Science Week on "Nano-enabling technologies", Houston, TX, USA, Nov. 14, 2012.

285. *Epitaxial growth of high quality vertical GaAs nanowires on graphene by molecular beam epitaxy*
A.M. Munshi, D.L. Dheeraj, V.T. Fauske, D.C. Kim, A.T.J. van Helvoort, B.O. Fimland, and **H. Weman**, Materials Res. Soc. 2012 Fall Meeting, Symposium FF: Semiconductor Nanowires-Optical and Electronic Characterization and Applications, Boston, MA, USA, Nov. 25 – Nov. 30, 2012.

286. *Semiconductor nanowires on graphene for next generation ICT*
H. Weman, (invited talk),
ITovation day 2012, Trondheim, Norway, Nov. 27, 2012.

287. *GaAs/AlGaAs core-shell nanowires for novel solar cell applications*
H. Kauko, A.M. Munshi, C.G. Lim, D.C. Kim, D.L. Dheeraj, B.O. Fimland, A.T.J. van Helvoort and **H. Weman,** Norwegian solar cell conference 2013, Oppdal, Norway, March 13-15, 2013.

288. *Epitaxial growth of vertical III-V semiconductor nanowires on graphene*
D.L. Dheeraj, A.M. Munshi, V.T. Fauske, D.C. Kim, A.T.J. van Helvoort, B.O. Fimland, and **H. Weman,** Graphene 2013, Bilbao, Spain, April 23-26, 2013.

289. *Epitaxial growth of vertical III-V semiconductor nanowires on graphene*
J. Nam, D.C. Kim, P.C. Andersen, S.J. Park, D.J. Dae, A.M. Munshi, D.L. Dheeraj, B.O. Fimland, and **H. Weman,** Korean Physical Society spring meeting, April 24-26, 2013.

290. *Epitaxial growth of vertical III-V semiconductor nanowires on graphene*
H. Weman (invited talk)
Int. conf. on Crystal Growth, Cancun, Mexico, June 10-13, 2013.

291. *Self-catalyzed MBE grown GaAs/GaAsSb core-shell nanowires in ZB and WZ crystal structures*
S.G. Ghalamestani, A.M. Munshi, D.L. Dheeraj, B.O. Fimland, **H. Weman**, and K.A. Dick,
7th Nanowire growth workshop, Lausanne, Switzerland, June 10-12, 2013.

292. *Limitations of self-catalytic growth in controlling diameter of GaAs nanowires on Si substrates*
A.M. Munshi, D.L. Dheeraj, V. T. Fauske, A.T.J. van Helvoort, B.O. Fimland, **H. Weman**,
7th Nanowire growth workshop, Lausanne, Switzerland, June 10-12, 2013.

293. *Epitaxial growth and characterization of vertical III-V semiconductor nanowires on graphene*
D.L. Dheeraj, A.M. Munshi, V.T. Fauske, D.C. Kim, A.T.J. van Helvoort, B.O. Fimland, and **H. Weman,**
7th Nanowire growth workshop, Lausanne, Switzerland, June 10-12, 2013.

294. *Semiconductor nanowires grown on graphene*
H. Weman (invited talk)
4th annual Nano network workshop, Bergen, Norway, June 17-19, 2013.

295. *Mechanical and electrical characterization of nanowire-substrate interfaces*
V.T. Fauske, D.C. Kim, A.M. Munshi, D.L. Dheeraj, B.O. Fimland, **H. Weman,** and A.T.J. van Helvoort
4th annual Nano network workshop, Bergen, Norway, June 17-19, 2013.

296. *Novel solar cells based on GaAs/AlGaAs core-shell nanowires*
H. Kauko, A.M. Munshi, C.G. Lim, D.C. Kim, D.L. Dheeraj, B.O. Fimland, A.T.J. van Helvoort and

H. Weman, 4th annual Nano network workshop, Bergen, Norway, June 17-19, 2013.

297. *Electrical properties of III-V semiconductor nanowires for solar cell applications*
J. Huh, D.C. Kim, H. Yun, A.M. Munshi, D.L. Dheeraj, G.T. Kim, A.T.J. van Helvoort, S.W. Lee, B.-O. Fimland, and **H. Weman,**
4th annual Nano network workshop, Bergen, Norway, June 17-19, 2013.

298. *GaAs nanowires grown on silicon and graphene for solar cell applications*
A.M. Munshi, D.L. Dheeraj, V.T. Fauske, D.C. Kim, J. Todorovic, J. Huh, S. Sandell, A.T.J. van Helvoort, B.O. Fimland, and **H. Weman,** 4th annual Nano network workshop, Bergen, Norway, June 17-19, 2013.

299. *Numerical analysis and device optimization of radial p-n junction GaAs/AlGaAs core- shell nanowire solar cells,*
C.G. Lim and **H. Weman,** 13th Int. Conf. on Numerical simulations of optoelectronic devices, Vancouver, Canada, Aug. 19-22, 2013. IEEE Xplore http://dx.doi.org/10.1109/NUSOD.2013.6633099.

300. *In-situ electrical and structural characterization of individual GaAs nanowires*
V.T. Fauske, D.C. Kim, A.M. Munshi, D.L. Dheeraj, B.O. Fimland, **H. Weman,** and A.T.J. van Helvoort EMAG 2013, York, UK, Sept. 2-6, 2013.

301. *Epitaxial growth of semiconductor nanowires on graphene: Generic model and potential device applications*
H. Weman (invited talk)
Crystal growth and graphene science, Boston, MA, USA, Sept. 4-5, 2013.

302. *Optical properties of self-catalyzed GaAs nanowires with axial GaAsSb inserts*
L. Ahtapodov, H. Kauko, A.M. Munshi, A.T.J. van Helvoort, B.O. Fimland, and **H. Weman,**
Nanowires 2013, Rehovot, Israel, Nov. 13-15, 2013.

303. *Design guidelines for radial p-n junction GaAs/AlGaAs core-shell nanowire solar cells*
C.G. Lim and **H. Weman,**
Nanowires 2013, Rehovot, Israel, Nov. 13-15, 2013.

304. *Effects on compositional variation on the electrical property of GaAsSb nanowires*
J. Huh, D.C. Kim, H. Yun, A.M. Munshi, D.L. Dheeraj, H. Kauko, A.T.J. van Helvoort, S.W. Lee, B.-O. Fimland, and **H. Weman**, Materials Res. Soc. 2013 Fall Meeting, Symposium SS: Nanowires and Nanotubes–Novel Materials, Advanced Heterostructures, Doping and Devices, Boston, MA, USA, Dec. 2 - Dec. 5, 2013.

305. *Inducing a direct-to-pseudodirect bandgap transition in wurtzite GaAs nanowires with uniaxial stress*
G. Signorello, E. Lörtscher, P.A. Khomyakov, S. Karg, D.L. Dheeraj, B. Gotsmann, **H. Weman** and H. Riel, Materials Res. Soc. 2014 Spring Meeting, Session UU: Semiconductor Nanowires-Synthesis, Properties and Applications, San Francisco, CA, USA, Apr. 21 - Apr. 25, 2014.

306. *Position Controlled GaAs Nanowires on Si Wafers using Nanoimprint Lithography*
A. M. Munshi, D.L. Dheeraj, D.C. Kim, J. Huh, J.F. Reinertsen, L. Ahtapodov, B.O. Fimland, **H. Weman,** V.T. Fauske, A.T.J. van Helvoort, K.D. Lee, and B. Heidari,
Materials Res. Soc. 2014 Spring Meeting, Session UU: Semiconductor Nanowires-Synthesis, Properties and Applications, San Francisco, CA, USA, Apr. 21 - Apr. 25, 2014.

307. *Enhancing the light-matter interactions in radial p-n junction core-shell nanowire solar cells above the planar junction limit for highly efficient semiconductor nanowire solar cells*
C.G. Lim and, **H. Weman,**
Materials Res. Soc. 2014 Spring Meeting, Session F: Controlling the Interaction between Light and Semiconductor Nanostructures for Energy Applications, San Francisco, CA, USA, Apr. 21 - Apr. 25, 2014.

308. *How a Norwegian university project became the nanotech spin-off CrayoNano*
H. Weman (invited talk), International Forum on the Nanotechnology Commercialization,
Seoul, Korea, June 111-12, 2014.

309. *Towards flexible high-efficiency semiconductor nanowire/graphene solar cells*
H. Weman (invited talk), Nanofair 2014, 10th Int. Nanotechnology Symposium "New ideas for industry", Dresden, Germany, July 1-3, 2014.

310. *Towards low-cost, high-efficiency semiconductor nanowire/graphene solar cells*
H. Weman (invited talk)
1st Int. Symposium on Energy Challenges and Mechanics, Aberdeen, Scotland, July 8-10, 2014.

Book chapters and Reviews

311. *Heterostructured III-V nanowires with mixed crystal phases grown by Au-assisted molecular beam epitaxy*
D.L. Dheeraj, H.L. Zhou, A.F. Moses, T.B. Hoang, A.T.J. van Helvoort, B.O. Fimland, and **H. Weman**, Chapter 2 in the book "Nanowires", ed. Paola Prete, IN-TECH, Vienna, Austria, 2010 (26 pages), ISBN 978-953-7619-79-4. http://sciyo.com/books/show/title/nanowires

312. *III-antimonide nanowires*
H. Weman and D.L. Dheeraj
Chapter 5 in the book "Advances in III-V Semiconductor Nanowires and Nanodevices",eISBN 978-1-60805-052-9, Ed. Jianye Li, Deli Wang and Ray R. LaPierre, Bentham science publishers, Ch. 5, pp. 89-104, 2011.

313. *Advances in semiconductor nanowires grown on graphene*
A.M. Munshi and **H. Weman**,
Phys.Status Solidi RRL (Review article in focus issue on "Semiconductor Nanowires"), **7**, 713 (2013).